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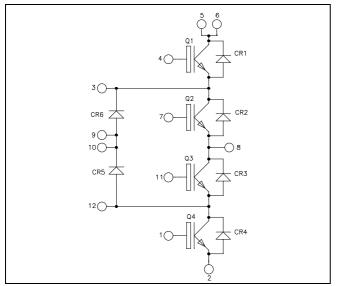
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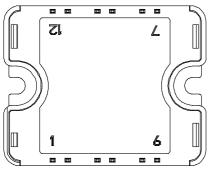
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## Three level inverter Trench + Field Stop IGBT3 **Power Module**





All multiple inputs and outputs must be shorted together 5/6; 9/10

Q1 to Q4	Absolute	maximum	ratings
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Symbol	Parameter		Max ratings	Unit
V <sub>CES</sub>	Collector - Emitter Breakdown Voltage		600	V
т	Continuous Collector Current	$T_C = 25^{\circ}C$	50	
I <sub>C</sub>	T T		30	А
I <sub>CM</sub>	Pulsed Collector Current	$T_C = 25^{\circ}C$	60	
$V_{GE}$	Gate – Emitter Voltage		±20	V
PD	Maximum Power Dissipation	$T_C = 25^{\circ}C$	90	W
RBSOA	Reverse Bias Safe Operating Area	$T_{\rm J} = 150^{\circ}{\rm C}$	60A @ 550V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

## APTGT30TL601G

## $V_{CES} = 600V$ $I_{\rm C} = 30 {\rm A}$ @ Tc = 80°C

#### Application

- Solar converter
- Uninterruptible Power Supplies

#### Features

- Trench + Field Stop IGBT3 Technology ٠
  - Low voltage drop \_
  - Low tail current \_
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
  - Very low stray inductance
- High level of integration

#### **Benefits**

- Stable temperature behavior •
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- **RoHS** Compliant



### All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

## Q1 to Q4 Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I <sub>CES</sub>	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 600V$				250	μA
V	Collector Emitter Saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		1.5	1.9	V
V <sub>CE(sat)</sub>	Conector Emitter Saturation Voltage	$I_C = 30A$	$T_{j} = 150^{\circ}C$		1.7		v
V <sub>GE(th)</sub>	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 400 \mu A$		5.0	5.8	6.5	V
I <sub>GES</sub>	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE}$	= 0V			300	nA

### Q1 to Q4 Dynamic Characteristics

-	Characteristic	Test Conditions		Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$			1600		
C <sub>oes</sub>	Output Capacitance	$V_{CE} = 25V$			110		pF
C <sub>res</sub>	Reverse Transfer Capacitance	f = 1 MHz			50		
Q <sub>G</sub>	Gate charge	$V_{GE} = \pm 15V, I_C = 300V$	30A		0.3		μC
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Switch	hing (25°C)		110		
T <sub>r</sub>	Rise Time	$V_{GE} = \pm 15V$			45		19.0
T <sub>d(off)</sub>	Turn-off Delay Time	$V_{Bus} = 300V$ $I_C = 30A$			200		ns
T <sub>f</sub>	Fall Time	$R_G = 10\Omega$		40		I	
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Switch	hing (150°C)		120		
T <sub>r</sub>	Rise Time	$V_{GE} = \pm 15V$ $V_{Bus} = 300V$			50		ns
T <sub>d(off)</sub>	Turn-off Delay Time	$I_C = 30A$			250		
T <sub>f</sub>	Fall Time	$R_G = 10\Omega$			60		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$	$T_j = 25^{\circ}C$		0.16		mJ
Lon	Turi-on Switching Energy	$V_{Bus} = 300V$	$T_{j} = 150^{\circ}C$		0.3		1115
E <sub>off</sub>	Turn-off Switching Energy	$I_C = 30A$	$T_j = 25^{\circ}C$		0.7		mJ
2011		$R_G = 10\Omega$	$T_{j} = 150^{\circ}C$		1.05		1110
I <sub>sc</sub>	Short Circuit data	$V_{GE} \le 15V$ ; $V_{Bus} = 360V$ $t_p \le 6\mu s$ ; $T_1 = 150^{\circ}C$			150		А
R <sub>thJC</sub>	Junction to Case Thermal Resistance					1.6	°C/W



## APTGT30TL601G

#### **CR1 to CR4 diode ratings and characteristics**

Symbol	Characteristic	Test Conditions	Test Conditions		Тур	Max	Unit		
V <sub>RRM</sub>	Maximum Peak Repetitive Reverse Voltage			600			V		
I <sub>RM</sub>	Maximum Reverse Leakage Current	V <sub>R</sub> =600V	$T_i = 25^{\circ}C$ $T_i = 150^{\circ}C$			150 350	μA		
I <sub>F</sub>	DC Forward Current		$Tc = 80^{\circ}C$		20		Α		
V	$V_F$ Diode Forward Voltage $I_F = 20A$ $V_{GE} = 0V$		$T_i = 25^{\circ}C$		1.6	2	V		
V F		$V_{GE} = 0V$	$T_{i} = 150^{\circ}C$		1.5		v		
4	D		$T_i = 25^{\circ}C$		100				
t <sub>rr</sub>	Reverse Recovery Time		$T_{j} = 150^{\circ}C$		150		ns		
0	Deserve Deservers Change	$I_F = 20A$	$T_j = 25^{\circ}C$		1.1		чС		
Q <sub>rr</sub>	Reverse Recovery Charge	$V_{R} = 300V$ di/dt = 1600A/us		$di/dt = 1600 \text{ A}/\mu \text{s}$ $T_j = 150$	$T_{i} = 150^{\circ}C$		2.3		μC
Б			$T_i = 25^{\circ}C$		0.23		T		
E <sub>rr</sub>				$T_{j} = 150^{\circ}C$		0.50		mJ	
R <sub>thJC</sub>	Junction to Case Thermal Resistance					3.25	°C/W		

### CR5 & CR6 diode ratings and characteristics

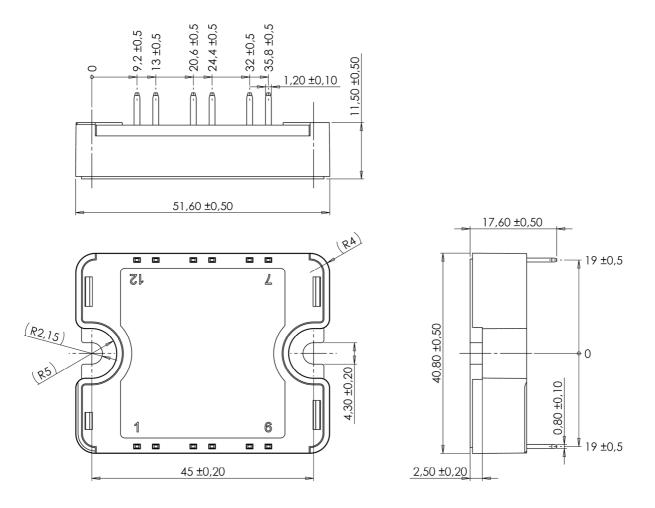
Symbol	Characteristic	Test Conditions	Test Conditions		Тур	Max	Unit
V <sub>RRM</sub>	Maximum Peak Repetitive Reverse Voltage			600			V
I <sub>RM</sub>	Maximum Reverse Leakage Current	V <sub>R</sub> =600V	$T_i = 25^{\circ}C$ $T_i = 150^{\circ}C$			150 350	μA
I <sub>F</sub>	DC Forward Current		$Tc = 80^{\circ}C$		30		Α
V <sub>F</sub>	Diode Forward Voltage	bltage $I_F = 30A$ $V_{GE} = 0V$	$T_i = 25^{\circ}C$		1.6	2	V
v F	Diode Porward Voltage		$T_{j} = 150^{\circ}C$		1.5		v
t <sub>rr</sub>	Reverse Recovery Time		$T_j = 25^{\circ}C$		100		ns
ι <sub>rr</sub>	Reverse Recovery Time		$T_{j} = 150^{\circ}C$		150		
0	Pavaraa Paaayary Charga	$I_{\rm F} = 30A$ $V_{\rm R} = 300V$ $di/dt = 1800A/\mu s$	$T_j = 25^{\circ}C$		1.5		чС
Q <sub>rr</sub>	Reverse Recovery Charge		$T_{i} = 150^{\circ}C$		3.1		μC
Б	Devience Decovery Energy		$T_i = 25^{\circ}C$		0.34		I m
E <sub>rr</sub>	Reverse Recovery Energy		$T_{j} = 150^{\circ}C$		0.75		mJ
R <sub>thJC</sub>	Junction to Case Thermal Resistance					2.45	°C/W

### Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
VISOL	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T <sub>J</sub>	Operating junction temperature range			-40		175	
T <sub>STG</sub>	Storage Temperature Range			-40		125	°C
T <sub>C</sub>	Operating Case Temperature					100	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight					80	g

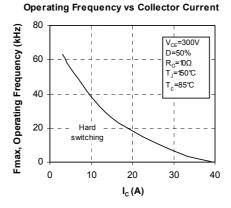


#### SP1 Package outline (dimensions in mm)



See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

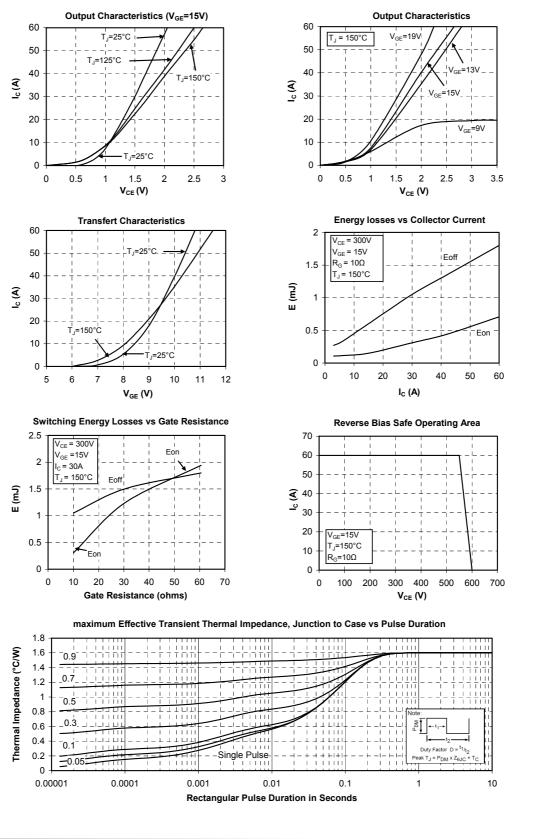
#### Q1 to Q4 Typical performance curve



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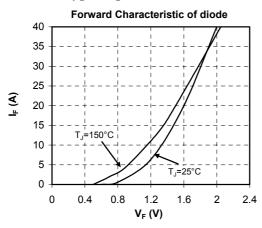
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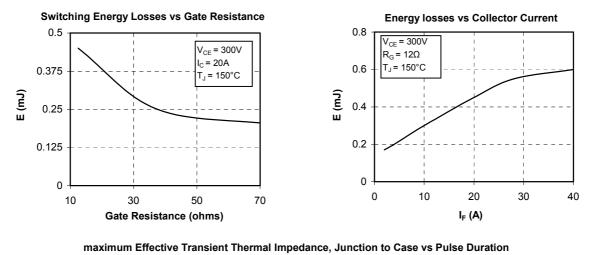


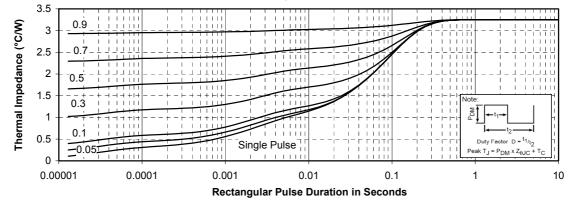
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#### **CR1 to CR4 Typical performance curve**

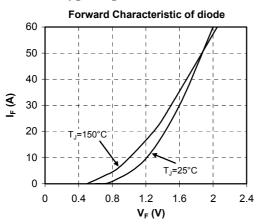


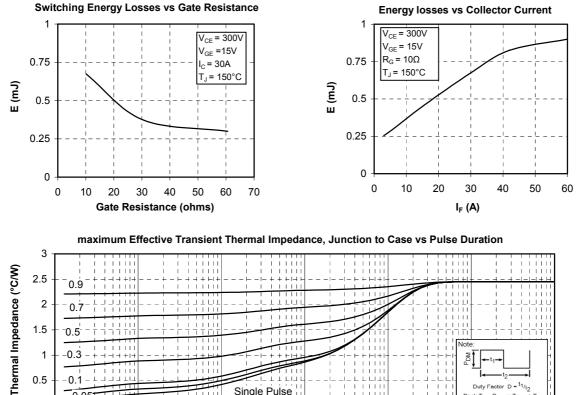


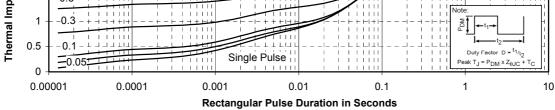




#### CR5 & CR6 Typical performance curve









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